

#### PCN# 20120820000 Qualification of MIHO8 as an Additional FAB Site Option for TPS92210/UCC28610 Select Devices in the LBC7 Process (includes design and datasheet revision) Change Notification / Sample Request

 Date:
 10/8/2012

 To:
 Newark PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (<u>PCN ww admin team@list.ti.com</u>).

Sincerely,

PCN Team SC Business Services Phone: +1(214) 480-6037 Fax: +1(214) 480-6659

#### **Products Affected:**

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

### DEVICE

### **CUSTOMER PART NUMBER**

TPS92210D UCC28610D UCC28610P null null null

Technical details of this Product Change follow on the next page(s).

PCN Number:			PCN20120820000					PCN Dat	te:	10/08/2012		
Title	of MI es in t	H( he	08 as ai e LBC7	n Additi Process	on (ir	al FAB Site Opti ncludes design a	on f and	or TPS922 datasheet	10/ rev	/UCC28610 ision)		
Cust	tome	r Contact:	PCN Manager Pt		Phone	e:	+1(214)480-6037		Dept:	Qι	uality Services	
*Proposed 1 <sup>st</sup> Ship Da			ate:	: 01/08/2013 Estimated Sample Availability:		ple			Date provided at sample request.			
Change Type:												
Assembly Site				Assembly Process				Assembly Materials				
Design		$\square$	$\leq$	Electrical Specification				Mechanical Specification				
Test Site				Packing/Shipping/Labeling				Test Process				
Wafer Bump Site				Wafer Bump Material				Wafer Bump Process				
🛛 🛛 Wafer Fab Site				Wafer Fab Materials				Wafer Fab Process				
PCN Details												
Description of Change:												

Texas Instruments is pleased to announce the qualification of its MIHO8 fabrication facility as an additional FAB option for select devices (shown in the Product Affected section). This change also includes a design and datasheet revision.

#### Design Revision: From Rev A to Rev C

Silicon fix to improve VGG clamp performance at high temperature.

#### **Datasheet Revision:**

<b>Device Family</b>	Change From:	Change To:
TPS92210	SLUS989A	SLUS989B
UCC28610	SLUS888E	SLUS888F

# Updated datasheet SLUS989B can be accessed by the following link: <a href="http://www.ti.com/product/tps92210">http://www.ti.com/product/tps92210</a>

	REVISION HISTORY					
Changes from Original (JANUARY 2010) to Revision A						
•	Changed Corrected Pin 2 name	1				
•	Changed Corrected Pin 2 name	12				
•	Changed location of Zener diode in Figure 19.	14				
Ch	nanges from Revision A (DECEMBER 2010) to Revision B	Page				
•	Added clarity to conditions in ELECTRICAL CHARACTERISTICS table	4				
•	Changed maximum PCL voltage specification from "1.05" to "1.1" in ELECTRICAL CHARACTERISTICS table	4				
•	Changed minimum I <sub>FM</sub> range for low power mode(LPM) modulation from "50" to "45" in ELECTRICAL CHARACTERISTICS table	4				
•	Added clarity to conditions in ELECTRICAL CHARACTERISTICS table	5				
•	Changed minimum TZE low clamp voltage from "-200" to "-220" in ELECTRICAL CHARACTERISTICS table	5				
•	Added clarity to FUNCTIONAL BLOCK DIAGRAM	6				
•	Added clarity to "conditions" statement in TYPICAL CHARACTERISTICS	8				
•	Added clarity to Figure 23	18				
•	Added clarity to Figure 24	19				

Changes from Revision E (July, 2011) to Revision F	Page
Changed updated typical application drawing on first page.	1
Changed Recommended Operating Conditions Application drawing.	
<ul> <li>Changed ESD Rating, Human Body Model from 2.0 kV to 1.5 kV.</li> </ul>	
Added Thermal Information Section.	
<ul> <li>Changed ELECTRICAL CHARACTERISTICS FB = 0 V to IFB = 10 µA.</li> </ul>	
Changed Voltage of CL pin max value from 1.05 V to 1.10 V.	
<ul> <li>Changed I<sub>FB</sub> range for Green Mode (GM) modulation min value from 50 µA to 45 µA.</li> </ul>	
Changed ZCD low clamp voltage min value from -200 mV to -220 mV.	
Changed ELECTRICAL CHARACTERISTICS FB = 0 V to IFB = 10 µA.	
Changed Figure 2.	
Changed Symplified Block Diagram	12
Changed Basic Flyback Converter and Waveforms at Peak Load and Minimum VBULK Voltage drawing	14
Changed Start-Up Currents for the Cascode Architecture drawing.	17
Changed Feedback Function text.	19
Changed FB Details drawing.	19
Changed Modulation Control Blocks drawing.	
Changed Control Diagram with Operating Modes drawing.	
Changed Figure 34.	
Changed High Frequency Ringing Solutions, (a) ferrite chip, (b) CDRV and (c) RG-OFF drawing.	

Fab Information					
Currently Qualified Sites, process, wafer dia.	Additional Site, process, wafer dia.				
DP1DM5, LBC7 Process, 200 mm	MIHO8, LBC7 Process, 200mm				

The LBC7 process was qualified at MIHO on 2005. Details are provided in the Qual Data Section.

#### **Reason for Change:**

- Improve device performance
- Increase long-term reliability
- Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

#### Changes to product identification resulting from this PCN:

# Die Rev designator and Wafer Fab Codes will change as shown in tables & sample label below:

Current	New
Die Rev [2P]	Die Rev [2P]
А	С

#### Wafer Fab Codes:

Current							
Chip Site	Chip site code (20L)	Chip country code (21L)					
DP1DM5	DM5	USA					
New							
Chip Site	Chip site code (20L)	Chip country code (21L)					
MIH08	MH8	JPN					

Sample product shipping label to indicate die rev and wafer fab code location (**not actual product label**)



#### **Product Affected:**

HPA00933DR	SN0901026DR	SN1011010DR	UCC28610D
HPA01021DR	SN1002004D	TPS92210D	UCC28610DR
HPA01125DR	SN1002004DR	TPS92210DR	UCC28610P
SN0901026D			

## **Qualification Data: Approved 9/14/2012**

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qual Vehicle 1: UCC28610						
Wafer Fab Site:	TI-MIHO	Wafer Fab Process:	LBC7			
Wafer Diameter:	200mm	Metallization:	Alu			
Passivation:	Nitride					

Qualification: 🗌 Plan 🛛 Test Results						
Reliability Test	Conditions	Sample Sample	Size/Fail t#2 Lot#	Lot#1 ±3		
Electrical Char.	-	Pass	-	-		
Latch-up	(per JESD78)	6/0	-	-		
Manufacturability (Assembly)	(per mfg. Site specification)	PASS	-	-		
Manufacturability (Test)	(per mfg. Site specification)	PASS	-	-		
ESD CDM	500V	3/0	-	-		
** Life Test	125C (168 Hrs)	79/0	-	-		
ESD HBM	1000V	3/0	-	-		
**Preconditioning sequence: MSL1-260C						

# **Reference Qualification (LBC7 Wafer Process in Miho8)**

Qualification Data: (Approved 01/14/2005)							
This qualification has be	This qualification has been specifically developed for the validation of this change. The qualification data						
validates that the propo	validates that the proposed change meets the applicable released technical specifications.						
		Qual Vehicle	1: TPS62110RSA				
Package Construction Details							
Wafer Fab Site:	Miho8		Wafer Fab Proces	s: LBC7			
Wafer Diameter:	200mm		Metallization	n: TiN/AlC	u.5/TiN		
Passivation:	Oxynitride 8	8000A					
Qualification:	Plan 🛛	<b>Test Results</b>					
Deliphility Test		Conditions		Sample Size / Fails			
Reliability Test		Conditions		Lot 1	Lot2	Lot 3	
**Life Test		140C (480 Hrs)		130/0	130/0	130/0	
**HAST		130C/85%RH (96 Hrs)		77/0	77/0	77/0	
**Autoclave		121C (96 Hrs)		77/0	77/0	77/0	
**Temp Cycle		-65C/150C (500 Cyc)		77/0	77/0	77/0	
**Thermal Shock		-65C/150C (500 Cyc)		77/0	77/0	77/0	
**High Temp. Storag	je Bake	170C (420 Hrs)		77/0	77/0	77/0	
ESD HBM		1000V		3/0	3/0	3/0	
ESD CDM		250V		3/0	3/0	3/0	
Latch-up		JESD78		5/0	5/0	5/0	
Wafer Level Reliabilit	y	Approved		Pass	Pass	Pass	
EFR	•	140C, 48 Hrs		626/0	636/0	619/0	
Manufacturability (Wa	afer Fab)	(per mfg. Site specification)		Pass	Pass	Pass	
**Preconditioning sequence: MSL2-260C							

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or to your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com